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RD 4: 0.2 to 1 mA; Rr 100 and above.		RD 2: 2 to mA; Rr 100 and above.	
		RD 3: 1 to 2 mA; Rr 150 and above.	
RD 5: 0.2 to 0.5 mA; Rr 100 (plus minus 1 V) and above.		RD 4: 0.2 to 1 mA; Rr 100 and above.	
		RD 5: 0.2 to 0.5 mA; Rr 100 (plus minus 1 V	) and above.
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RD 6 (rectifier of high sensitivity): 500 Ohm plus minus 12% at 70 mV; Rr 2 and above.

- Although development of the diodes and detectors is completed, they are produced in limited number only.

  Diodes and detectors are for use as rectifiers, meter 50X1-HUM rectifiers, demodulators, adjustable AC resistances, ring modulators, discriminators, limiters, A.V.C. generators, mixers, and distorters. Their frequency range includes audio frequency, carrier frequency, UKW, and highest frequency up to 3.2 centimeters.
- 4. Transistors are not yet under development at the enterprise, but there are plans to start transistor development in 1954. Dr. Falter (fnu)—and Dr. Haiber (fnu), who are the chief development technicians, view the development of diodes and detectors as a preliminary stage of transistor development, although they have strong doubts whether the enterprise will be able to tackle the problem of transistor development successfully. Dr. Haiber is rather skeptical with respect to the future of transistors. He has expressed the opinion that even in the United States the great hopes initially attached to the development of transistors have recently given way to disillusionment because of the difficulties of fabrication, high costs, and bad functioning. The plant has, nevertheless, submitted a proposal for the development of transistors in 1954. As of early October 1953, the Central Office for Research and Technology (ZAFT) had not approved the project.
- 5. Dralowid is also engaged in the development of resistances for telecommunications technology which stay constant in the temperature range
  from +50° to -70° Centigrade. The temperature
  coefficient is ten power minus five, an improvement over the value thus
  far attained in East Germany (ten power minus four).

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1/	Comment.	previous	50X1-HUN
		transistor development	50X1-HUM
		probably referred to the development of germanium diodes, which was interpreted as an initial step in transistor development.	33X1 110W

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